EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	114347	ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:44
L2	13515	dry near clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:44
L3	1584	plasma near clean	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:44
L4	14968	2 or 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:44
L5	16	1 near 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:53
L6	0	5 and cluster	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:44
L7	216412	etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:53
L8	45	3 near 7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:53
L10	325	etch near ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:54

EAST Search History

L11	0	(plasm near etch) near (plasma near ash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:54
L12	19	(plasma near etch) near (plasma near ash)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:54
L13	953	centura	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 09:54
L14	19	13 and etch and ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:10
L15	2	"6440864".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:37
L17	75	cassette near storage near shelves	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:22
L19	28	automated and (cassette near storage near shelves)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:23
L20	1664201	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:23
L21	9	19 and 20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:30
L22	1	residue near removal near passivation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:43

EAST Search History

L24	2	60/293,805	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:32
L35	0	etch near deposition near Centura	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:13
L36	6	(etch near deposition) same Centura	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:13
L37	881	remote near plasma near source	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:39
L38	129115	watt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:40
L39	458	kwatt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:40
L40	0	37 near 39	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:39
L41	0	37 near 38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:39
L42	9	rf near kwatt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:40
L43	1441	rf near watt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:40

EAST Search History

L44	1448	42 or 43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:40
L45	94	37 and 44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:41
L46	0	45 and centura	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:41
L47	94	45 and applied	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:41
L48	88	45 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:41
L49	5	48 and tantalum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:42
L50	81	48 and (tantalum or metal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:46
L51	0	50 and ("5000" near kwat)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:46
L52	21	50 and ("5000" near watt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:50
L53	0	50 and ("10000" near watt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:46

L54	0	50 and ("20000" near watt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:47
L55	1	50 and ("30000" near watt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:47
L56	1	50 and ("30" near kwatt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:48
L57	0	50 and ("20" near kwatt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:48
L58	1	50 and ("10" near kwatt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:48
L59	1	50 and ("5" near kwatt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 11:48
L60	9	09/632669	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 12:15
L61	2683	438/706	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 12:16
L62	0	216/345.11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 12:15
L63	219	156/345.11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 12:15

L64	394	438/707	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 12:16
L65	322	438/708	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2006/06/06 12:16
L66	348	438/709	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 12:16
S2	216002	etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 15:47
S3	3657002	metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 15:47
S4	1000799	silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 15:47
S6	2909	insitu	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:20
S7	46992	in-situ	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:26
S8	49352	S6 or S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:26
S9	216196	etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:27

S10	3658720	metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:27
S11	1001589	silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:27
S12	6006	S8 and S9 and S10 and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:27
S13	0	S8 near S9 near (S10 and S11)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:28
S14	9	(S8 near S9) same (S10 and S11)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:35
S15	123273	cluster	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:35
S16	114275	ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:36
S17	629515	residue	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:36
S19	605	S15 and S16 and S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:36
S20	97	S19 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:36

S21	473981	S10 and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:37
S22	86	S20 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:44
S23	532273	(etch or etching or etcher)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:45
S24	5209	cluster adj (tool or system or apparatus)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 09:45
S25	4	S23 near S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:01
S26	1592	centura or endura	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:01
S29	13690	applied adj materials.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:01
S30	493	S26 and S29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:02
S31	174937	"28" and S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:03
S33	416	S23 and S30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:03

EAST Search History

S34	496	etch near (metal and silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:03
S35	5	S33 and S34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:11
S36	665207	LCD or LED	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:11
S37	49117	first near metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:11
S38	46967	second near metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:12
S39	18175	first near silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:12
S40	14875	second near silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:12
S41	1030	multilayer near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:12
S42	423	S37 and S38 and S39 and S40	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:13
S43	0	S42 and S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:13

EAST Search History

S44	440500	resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:13
S45	147	S42 and S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:01
S46	11	S45 and S36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 10:13
S47	36877	pixel adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:01
S48	6724	thin adj film adj resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:02
S49	43574	S47 or S48	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:02
S50	219946	LCD	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:02
S51	15815	S49 and S50	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:03
S52	12	S51 and S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:27
S53	2	"5478766".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:28

EAST Search History

S54	2	"20020038893"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:52
S55	2	resist near over near metal near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:53
S56	2	resist near over near metal adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:53
S57	40	resist near metal adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:54
S58	0	(mutiple near layers near resist) near metal adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:54
S59	0	(mutiple near layers near resist) near (metal adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:54
S60	0	(mutiple near layers near resist) near (metal near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:55
S61	0	(mutiple near resist) near (metal adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:55
S62	0	(mutiple near resist) with (metal adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:55
S63	0	(mutiple near resist) same (metal adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:55

EAST Search History

S64	9203	(metal adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:55
S65	440500	resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:55
S66	56	S65 near S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:58
S67	370	(multi or multiple) near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:57
S68	559	(multi or multiple) near layers near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:56
S69	0	S67 near S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:56
S70	1	triple adj resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:57
S71	96	double adj resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:57
S72	0	S71 same S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:57
S73	0	S66 and multiple near resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:58

EAST Search History

S74	0	S66 and (multiple near resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 11:58
S75	19	S66 and (layers near resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:04
S76	11426	metal near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:12
S77	440500	resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:11
S78	216196	etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:11
S79	321	form near metal near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:13
S80	146	S79 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:12
S81	11	S79 near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:12
S82	2	form near tantalum near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:14
S83	88	tantalum near mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:14

EAST Search History

S84	3	S52 and resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 12:27
S85	7553	pixel adj portion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 14:56
S86	0	(source adj drain) near (pixel adj portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 14:57
S87	368	(source adj drain) same (pixel adj portion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:09
S88	64	multi-level adj resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:09
S89	6493	remove near silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:09
S90	0	S88 and S89	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:09
S91	1001589	silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:09
S92	51	S88 and S91	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:13
S93	0	S92 and (metal near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:13

EAST Search History

S94	1	MLR and (metal near mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:14
S95	9203	(metal adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:15
S96	1	resit near levels	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:15
S97	689	resist near levels	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:15
S98	1160	(resist or photoresist) near levels	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:15
S99	25	S95 and S98	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:19
S100	2	"5160404".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:27
S101	3	"7008808".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:41
S102	0	(etch or etching) near metal adj layer near expose near silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:42
S103	18	(etch or etching) near (metal adj layer) near silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:43

EAST Search History

S10 4	28376	(etch or etching) near silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:45
S10 5	363	S104 and (metal adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:43
S10 6	195	S105 and resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:45
S10 7	2180166	etch or etching or remove	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:45
S10 8	22667	doped adj silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:45
S10 9	481013	LED or (liquid adj electrode adj display)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:48
S11 0	230	S107 near S108	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:47
S11 1	215530	S109 and "23"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:47
S11 2	15	S109 and S110	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:47
S11 3	1	10/821723	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/06 10:20

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S11 4	49495	LED and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:49
S11 5	489	216/58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:50
S11 6	16038	"same" near chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:59
S11 7	324	ash near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:59
S11 8	0	S116 near S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:59
S11 9	3	S116 with S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 16:59
S12 0	5	S116 same S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:24
S12 1	0	etch near ash near one near chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:24
S12 2	12	etch near ash near chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:25
S12 3	0	etch near ash near claen near chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:25

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EAST Search History

S12 4	4816	TEL.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:25
S12 5	0	Dual adj Frequency adj Confined adj Technology	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 17:26
S12 6	8	Dual Frequency Confined	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:27
S12 7	2436	ash and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:27
S12 8	0	S126 and S127	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:27
S12 9	16	Exelan "2300"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:27
S13 0	2436	ash and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:27
S13 1	2	S129 and S130	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:27
S13 2	0	in-situ near etch near ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:28
S13 3	0	(in adj situ) near etch near ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:28

EAST Search History

S13 4	324	etch near ash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:28
S13 5	36	etch near ash.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:30
S13 6	2	"20020179248"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/06/01 17:30
S13 7	2	"20020132488"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:08
S13 8	40	second near gas near process near chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:52
S13 9	0	second near gas near (oxygen and chlorine) near chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:52
S14 0	15	second near gas near (oxygen or chlorine) near chamber	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:54
S14 1	1	(oxygen and chlorine) near second near gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:55
S14 2	37481	second near gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:56
S14 3	114197	(oxygen and chlorine)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:56

S14 4	365289	second same gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:57
S14 5	36887	(oxygen same chlorine)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:56
S14 6	1168	S144 same S145	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:56
S14 7	545	S146 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:56
S14 8	20673	second adj gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:57
S14 9	71	S148 same S146	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 10:57
S15 0	55	S149 and S147	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:08
S15 1	0	S150 and "BCL.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:08
S15 2	4	S150 and BCL3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:10
S15 3	216255	etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:10

S154	474062	metal and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:11
S155	78481	S153 and S154	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:11
S156	19851	metal near silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:11
S157	36	S153 near S156	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:11
S158	5	S157 and second near gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:14
S159	535	carbon near containing near fluorine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:15
S160	2573602	gases	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:14
S161	27	etch near metal near silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:15
S162	110	S159 near S160	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:16
S163	0	S161 and S162	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:15

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S16 4	47	S162 and oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 11:17
S16 5	14	S162 and oxygen and chlorine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:47
S16 6	1812	cluster adj system	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:47
S16 7	2180681	etch or remove or etching	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:48
S16 8	524	S166 and S167	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:48
S16 9	21775	(first and second) near gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:51
S17 0	5	S168 and S169	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:49
S17 3	13703	applied adj material.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:51
S17 4	824	S173 and cluster	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:51
S17 5	473	S174 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:51

S17 6	39	S175 and S169	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:54
S17 7	20	bcl3 and sf6 and nf3 and (oxygen or o2) and chlorine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:54
S17 8	0	S173 and S177	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:55
S17 9	1372	(BCL3 or BCLx or BCLn or BCLsubx or BCLsubn or "B.CL.subx" or "B.CL. subn" or "B.CL.sub.x" or "B.CL.sub. n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:28
S18 0	6639	(SF6 or SFx or SFn or SFsubx or SFsubn or "SF.subx" or "SF.subn" or "SF.sub.x" or "SF.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:55
S18 1	1604	(NF3 or NFx or NFNF or NFsubx or NFsubNF or "NF.subx" or "NF. subNF" or "NF.sub.x" or "NF.sub. NF")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:55
S18 2	2204113	(oxygen or O2 or Ox or On or Osubx or Osubn or "O.subx" or "O. subn" or "O.sub.x" or "O.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:56
S18 3	26	S179 and S180 and S181 and S182	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:56
S18 4	25	S183 and etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:56
S18 5	37481	second near gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:57

S18 6	6	S184 and S185	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 13:57
S18 7	0	meatal near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:23
S18 9	3463	remote near plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:23
S19 0	0	S187 and S189	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:23
S19 1	6091	metal near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:23
S19 2	109	S189 and S191	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:23
S19 3	51	S192 and tantalum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:28
S19 4	0	S179 near first near gas	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:29
S19 5	0	second near process near gass near chlorine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:29
S19 6	10	second near process near gas near chlorine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:33

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S19 7	3	S196 and S169	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:40
S19 8	2	"20010055852"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 14:40
S20 0	3463	remote near plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:08
S20 1	953	centura	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:08
S20 2	118	S200 and S201	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:33
S20 3	592	second near gas near oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:33
S20 4	213	etch near tantalum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:33
S20 5	1	S203 and S204	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:53
S20 6	6	09/614,396	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/05 15:53